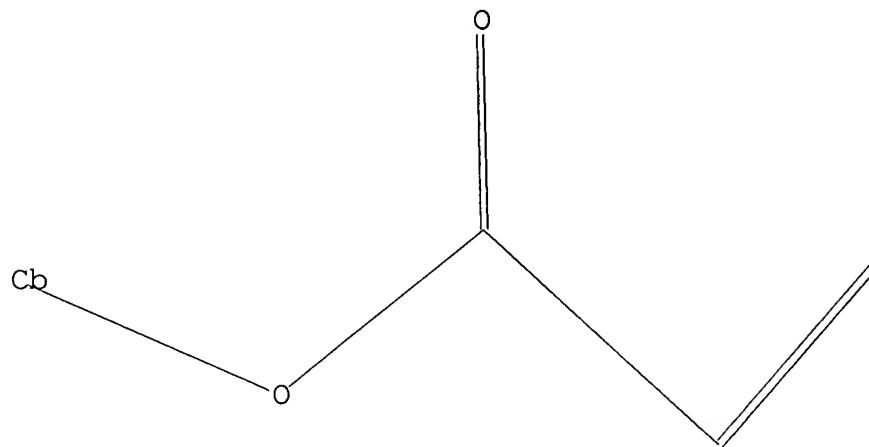


L1        STRUCTURE UPLOADED

=> D L1

L1 HAS NO ANSWERS

L1                    STR



Structure attributes must be viewed using STN Express query preparation.

=> S L1

SAMPLE SEARCH INITIATED 13:52:22 FILE 'REGISTRY'

SAMPLE SCREEN SEARCH COMPLETED - 64399 TO ITERATE

3.1% PROCESSED        2000 ITERATIONS

50

ANSWERS

INCOMPLETE SEARCH (SYSTEM LIMIT EXCEEDED)

SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS:    ONLINE    \*\*INCOMPLETE\*\*  
                              BATCH    \*\*COMPLETE\*\*

PROJECTED ITERATIONS:        1272872 TO    1303088

PROJECTED ANSWERS:            39738 TO        45268

L2                    50 SEA SSS SAM L1

=> FILE CAPLUS

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

0.86

1.13

FILE 'CAPLUS' ENTERED AT 13:52:36 ON 07 SEP 2005

USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.

PLEASE SEE "HELP USAGETERMS" FOR DETAILS.

COPYRIGHT (C) 2005 AMERICAN CHEMICAL SOCIETY (ACS)

SAMPLE SEARCH INITIATED 13:52:43 FILE 'REGISTRY'  
SAMPLE SCREEN SEARCH COMPLETED - 64399 TO ITERATE

3.1% PROCESSED 2000 ITERATIONS  
ANSWERS  
INCOMPLETE SEARCH (SYSTEM LIMIT EXCEEDED)  
SEARCH TIME: 00.00.01

50

FULL FILE PROJECTIONS: ONLINE \*\*INCOMPLETE\*\*  
BATCH \*\*COMPLETE\*\*  
PROJECTED ITERATIONS: 1272872 TO 1303088  
PROJECTED ANSWERS: 39738 TO 45268

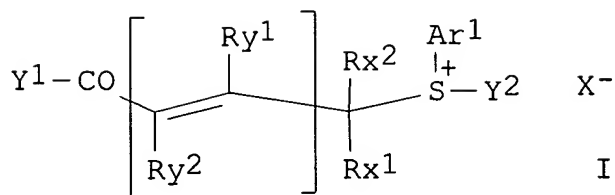
L3 50 SEA SSS SAM L1

L4 48 L3

=> D L4 IBIB ABS HITSTR 1-48

L4 ANSWER 1 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
ACCESSION NUMBER: 2005:522626 CAPLUS  
DOCUMENT NUMBER: 143:35151  
TITLE: Chemically amplified positive-working far-UV  
photoresists and their patterning method  
INVENTOR(S): Kodama, Kunihiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 49 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
DATE	----	-----	-----
-----			
JP 2005156821	A2	20050616	JP 2003-393871
20031125			
PRIORITY APPLN. INFO.:			JP 2003-393871
20031125			
GI			



AB The photoresists contain polymers having single-ring or polycyclic alicyclic hydrocarbon structure and increasing solubility in alkaline developers upon acid action, and sulfonium salt photoacid generators I [Y1 = aryl, (cyclo)alkyl, alkenyl; Y2 = aryl, (cyclo)alkyl; RX1-2 = H, alkyl, aryl, aralkyl; RY1-2 = H, alkyl, aryl; Ar1 = aryl; X- = non-nucleophilic anion; n = 0-2; Ar1 and Y2, RX1 and RX2, Y1 and RX, Y1 and RY1, and Y1 and RY2 may form a ring]. The photoresists provide good profile patterns regardless of the temperature of post-exposure baking.

IT 848413-54-7

RL: TEM (Technical or engineered material use); USES (Uses) (in chemical amplified pos.-working far-UV photoresist containing sulfonium salt photoacid generator and its lithog.)

RN 848413-54-7 CAPLUS

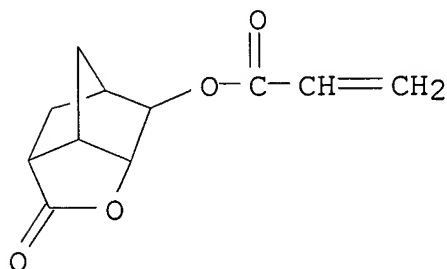
CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer

with 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl 2-methyl-2-propenoate, hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 2-methyl-2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 242129-35-7

CMF C11 H12 O4



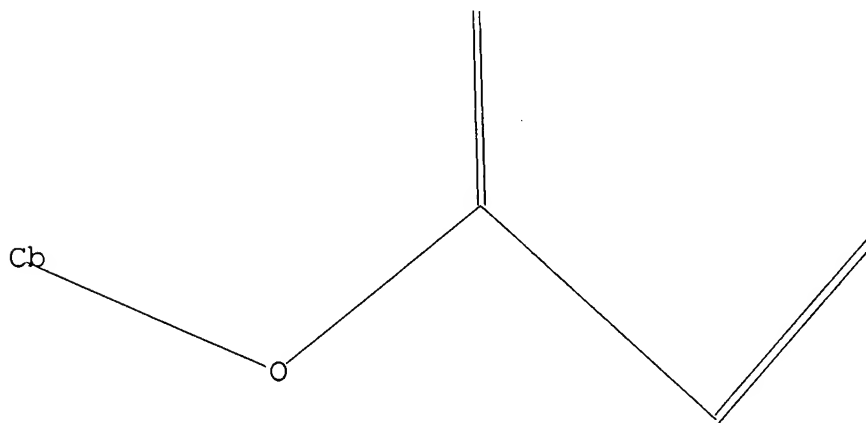
Copyright of the articles to which records in this database refer is held by the publishers listed in the PUBLISHER (PB) field (available for records published or updated in Chemical Abstracts after December 26, 1996), unless otherwise indicated in the original publications. The CA Lexicon is the copyrighted intellectual property of the American Chemical Society and is provided to assist you in searching databases on STN. Any dissemination, distribution, copying, or storing of this information, without the prior written consent of CAS, is strictly prohibited.

FILE COVERS 1907 - 7 Sep 2005 VOL 143 ISS 11  
FILE LAST UPDATED: 6 Sep 2005 (20050906/ED)

New CAS Information Use Policies, enter HELP USAGETERMS for details.

This file contains CAS Registry Numbers for easy and accurate substance identification.

=> D L1  
L1 HAS NO ANSWERS  
L1 STR



Structure attributes must be viewed using STN Express query preparation.

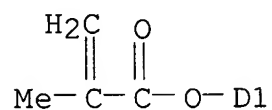
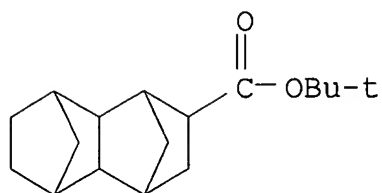
=> S L1  
**REGISTRY INITIATED**  
Substance data SEARCH and crossover from CAS REGISTRY in progress...  
Use DISPLAY HITSTR (or FHITSTR) to directly view retrieved structures.

CM 2

CRN 195398-50-6

CMF C21 H30 O4

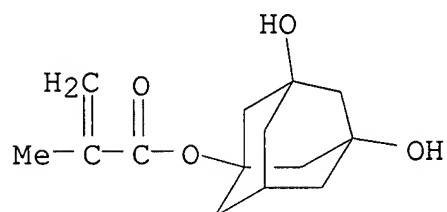
CCI IDS



CM 3

CRN 115522-15-1

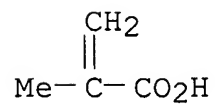
CMF C14 H20 O4



CM 4

CRN 79-41-4

CMF C4 H6 O2



DOCUMENT NUMBER: 142:400564  
 TITLE: Positive-working photoresist composition  
 containing specific acid generator and method for  
 pattern formation using the same  
 INVENTOR(S): Kodama, Kunihiro; Wada, Kenji; Sato,  
 Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 60 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
JP 2005099556	A2	20050414	JP 2003-334830
20030926			
PRIORITY APPLN. INFO.: 20030926			JP 2003-334830

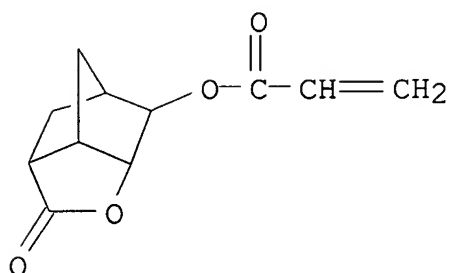
AB The title composition contains an acid-sensitive  
 alkali-solubilizable resin  
 having an alicyclic hydrocarbon structure and an actinic ray- or  
 radiation-sensitive acid generator, wherein the acid generator  
 has structure (Y1)(Y2)(Ar)S+ ( Ar = aryl; Y1-2 = alkyl, cycloalkyl)  
 and generates sulfonic acid A1-(A2-SO3H) (A1 = n-valent connecting  
 group; A2 =  
 1- or 2-valent aliphatic group; n = integer 2-4). The  
 composition shows low temperature  
 dependence of post exposure baking process and provides good  
 pattern profile.

IT **848413-54-7P**  
 RL: SPN (Synthetic preparation); TEM (Technical or engineered  
 material use); PREP (Preparation); USES (Uses)  
 (acid generator in pos.-working photoresist composition)  
 RN 848413-54-7 CAPLUS  
 CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or  
 7)-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester,  
 polymer  
 with 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl  
 2-methyl-2-propenoate,  
 hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl  
 2-propenoate and  
 2-methyl-2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 242129-35-7

CMF C11 H12 O4

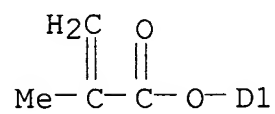
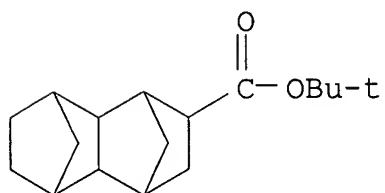


CM 2

CRN 195398-50-6

CMF C21 H30 O4

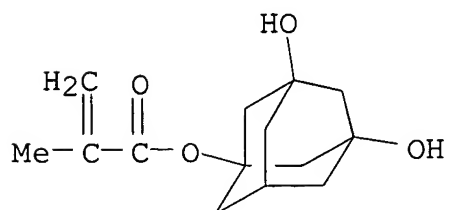
CCI IDS



CM 3

CRN 115522-15-1

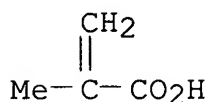
CMF C14 H20 O4



CM 4

CRN 79-41-4

CMF C4 H6 O2



L4 ANSWER 3 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN

ACCESSION NUMBER: 2005:302552 CAPLUS

DOCUMENT NUMBER: 142:382176

TITLE: Positive-working resist composition  
containing

sulfonic acid generator and method of  
forming pattern  
using the same

INVENTOR(S): Kodama, Kunihiro; Wada, Kenji; Sato,  
Kenichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 62 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
DATE	-----	----	-----

JP 2005092053	A2	20050407	JP 2003-328062
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20030919  
PRIORITY APPLN. INFO.: JP 2003-328062  
20030919

OTHER SOURCE(S): MARPAT 142:382176

AB Disclosed is a pos.-working resist composition comprising (a) a  
resin which has

a monocyclic or polycyclic alicyclic hydrocarbon structure and  
is able to

increase its soluble in an alkali developer upon an interaction  
with an acid,

(b) a compound generating sulfonic acid A1-(A2-SO3H)<sub>n</sub> (A1 = n  
valent bonding

group; A2 = single bond or divalent aliphatic group; and n =  
2-4) upon

receiving an active ray or radiation, and (c) a basic compound  
R250R251R252N



(R250 = alkyl; R251,252 = H, alkyl, cycloalkyl, aryl, may form ring together).

IT 848413-54-7P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (pos.-working resist composition containing sulfonic acid generator)

RN 848413-54-7 CAPLUS

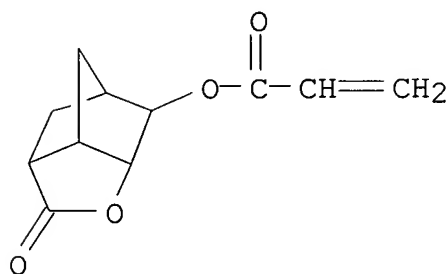
CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer

with 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl 2-methyl-2-propenoate, hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 2-methyl-2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 242129-35-7

CMF C11 H12 O4

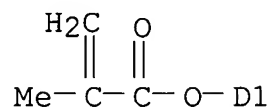
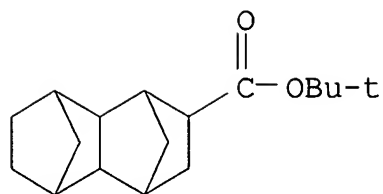


CM 2

CRN 195398-50-6

CMF C21 H30 O4

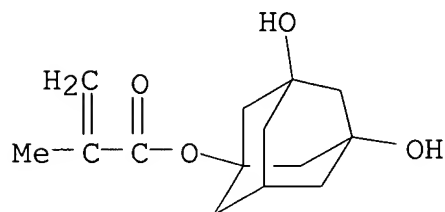
CCI IDS



CM 3

CRN 115522-15-1

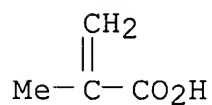
CMF C14 H20 O4



CM 4

CRN 79-41-4

CMF C4 H6 O2



L4 ANSWER 4 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
 ACCESSION NUMBER: 2005:259482 CAPLUS  
 DOCUMENT NUMBER: 142:345153  
 TITLE: Positive resist composition and  
 pattern-forming method  
 INVENTOR(S): Yasunami, Shoichiro; Wada, Kenji; Kodama,  
 Kunihiro;  
 Sato, Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: U.S. Pat. Appl. Publ., 42 pp.

DOCUMENT TYPE: CODEN: USXXCO  
 LANGUAGE: Patent  
 English  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
US 2005064326	A1	20050324	US 2004-941822
JP 2005122133	A2	20050512	JP 2004-262469
PRIORITY APPLN. INFO.:			JP 2003-328063 A
			JP 2003-331457 A

AB A pos. resist composition includes: (A) a resin capable of increasing a solubility in an alkali developer by an action of an acid; (B) a compound capable of generating a sulfonic acid upon irradiation with one of an actinic ray and a radiation represented by the following formula (1):  $A_1(A_2-SO_3H)_n$  (A1 = n-valent linking group, A2 = single bond, divalent aliphatic; provided that at least one group represented by A1 or A2 contains fluorine; n = 2-4); and (C1) at least one of an amine compound having at least an aliphatic hydroxyl group in a mol. and an amine compound having at least an ether bond in a mol. The object of the present invention is to provide a pos. resist composition excellent in resolution, and also excellent in the margin of exposure amount and PEB temperature dependency even in forming minute patterns of 100 nm or less.

IT 848413-54-7P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (resin; pos. resist composition and pattern-forming method)

RN 848413-54-7 CAPLUS

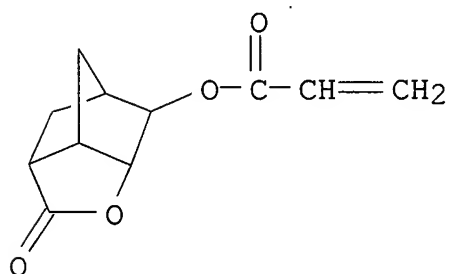
CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer with 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl 2-methyl-2-propenoate,

hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl  
 2-propenoate and  
 2-methyl-2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 242129-35-7

CMF C11 H12 O4

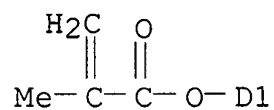
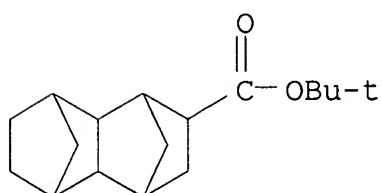


CM 2

CRN 195398-50-6

CMF C21 H30 O4

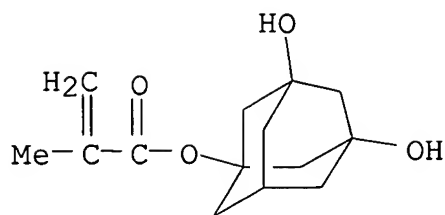
CCI IDS



CM 3

CRN 115522-15-1

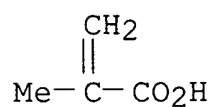
CMF C14 H20 O4



CM 4

CRN 79-41-4

CMF C4 H6 O2



L4 ANSWER 5 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
 ACCESSION NUMBER: 2005:253318 CAPLUS  
 DOCUMENT NUMBER: 142:345147  
 TITLE: Photosensitive composition and pattern  
 forming method  
 using the same  
 INVENTOR(S): Kodama, Kunihiro; Wada, Kenji; Satoh,  
 Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Eur. Pat. Appl., 146 pp.  
 CODEN: EPXXDW  
 DOCUMENT TYPE: Patent  
 LANGUAGE: English  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
EP 1517179	A1	20050323	EP 2004-21460
20040909			
R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, PL, SK, HR			
JP 2005122134	A2	20050512	JP 2004-262499
20040909			
US 2005095532	A1	20050505	US 2004-937270
20040910			
PRIORITY APPLN. INFO.:			
20030910			JP 2003-318276 A

20030919 JP 2003-327608 A

JP 2003-333503 A

20030925

OTHER SOURCE(S): MARPAT 142:345147

AB The present invention relates to a photosensitive composition containing a compound capable of generating a specific acid having the plural number of sulfonic groups by irradiation with an actinic ray or a radiation and a pattern forming method using the same.

IT **848413-54-7P**

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (photosensitive composition for pattern forming method containing)

RN 848413-54-7 CAPLUS

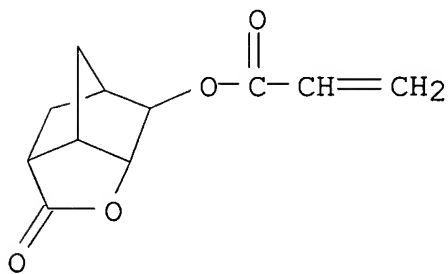
CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer

with 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl 2-methyl-2-propenoate, hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 2-methyl-2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 242129-35-7

CMF C11 H12 O4

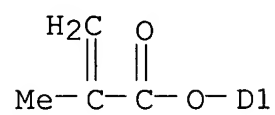
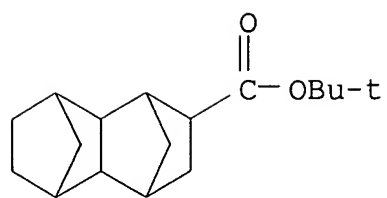


CM 2

CRN 195398-50-6

CMF C21 H30 O4

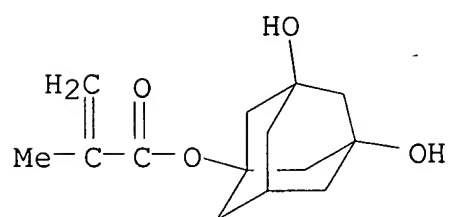
CCI IDS



CM 3

CRN 115522-15-1

CMF C14 H20 O4



L4 ANSWER 17 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
 ACCESSION NUMBER: 2001:115197 CAPLUS  
 DOCUMENT NUMBER: 134:185945  
 TITLE: Polymer for photoresists and resin  
 compositions for photoresists  
 INVENTOR(S): Funaki, Yoshinori; Tsutsumi, Kiyoharu;  
 Takaragi, Akira; Inoue, Keizo  
 PATENT ASSIGNEE(S): Daicel Chemical Industries, Ltd., Japan  
 SOURCE: PCT Int. Appl., 152 pp.  
 CODEN: PIXXD2  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
WO 2001010916	A1	20010215	WO 2000-JP5168
20000802			
W: KR, US			
RW: DE, FR, GB			
JP 2001048931	A2	20010220	JP 1999-223110
19990805			
JP 3390702	B2	20030331	
JP 2001048933	A2	20010220	JP 1999-223144
19990805			
JP 3330903	B2	20021007	
EP 1172384	A1	20020116	EP 2000-949953
20000802			
R: DE, FR, GB			
TW 513618	B	20021211	TW 2000-89115561
20000803			
US 6692889	B1	20040217	US 2001-806857
20010405			
PRIORITY APPLN. INFO.:			
19990805			JP 1999-223110 A
			JP 1999-223144 A
19990805			WO 2000-JP5168 W
20000802			
GI			

\* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY - AVAILABLE VIA OFFLINE PRINT \*



AB A polymer comprises at least one kind of monomer units selected from I-IV

(R1 = H, Me; R2,3 = H, OH, etc.; R5,6 = H, OH, CO; R7-9 = H, Me; R10,11 =

C1-8 hydrocarbon; R12-14 = H, OH, Me), with the proviso that when the polymer comprises monomer units of III. It must also contain at least

another kind of monomer units selected from among those represented by

general formula V (R15,16 = H, OH, COOH; R17 = OH, CO, COOH) or the like.

This polymer is excellent not only in transparency, solubility in alkali and

tight adhesion but also in etching resistance, thus being useful as the

resin for photoresists.

IT 325991-46-6P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material

use); PREP (Preparation); USES (Uses)

(polymer for photoresists and resin compns. for photoresists)

RN 325991-46-6 CAPLUS

CN 2-Propenoic acid,

1,5-dihydroxy-2-methyltricyclo[3.3.1.1<sup>3,7</sup>]dec-2-yl

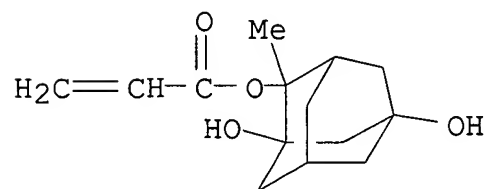
ester, polymer with 2-methyltricyclo[3.3.1.1<sup>3,7</sup>]dec-2-yl 2-propenoate

(9CI) (CA INDEX NAME)

CM 1

CRN 325991-12-6

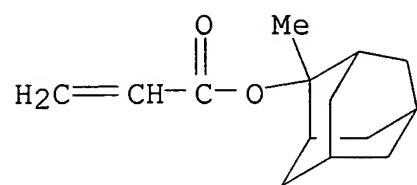
CMF C14 H20 O4



CM 2

CRN 249562-06-9

CMF C14 H20 O2



REFERENCE COUNT:

12

THERE A

REFERENCE COUNT: 14 THERE ARE 14 CITED REFERENCES  
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RE FORMAT

L4 ANSWER 10 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
ACCESSION NUMBER: 2003:912697 CAPLUS  
DOCUMENT NUMBER: 139:401549  
TITLE: Polymers, resist compositions and patterning  
process  
INVENTOR(S): Harada, Yuji; Hatakeyama, Jun; Sasago,  
Masaru; Endo,  
Masayuki; Kishimura, Shinji  
PATENT ASSIGNEE(S): Japan  
SOURCE: U.S. Pat. Appl. Publ., 22 pp.  
CODEN: USXXCO  
DOCUMENT TYPE: Patent  
LANGUAGE: English  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.
US 2003215740	A1	20031120	US 2003-396556
20030326			
JP 2004002720	A2	20040108	JP 2003-73273
20030318			
PRIORITY APPLN. INFO.:			JP 2002-85547 A
20020326			JP 2002-85598 A
20020326			

AB A resist composition comprises a base polymer having sulfone or sulfonate units introduced therein is sensitive to high-energy radiation below 300 nm, is endowed with excellent adherence to substrates while maintaining transparency, and is suited for lithog. microprocessing.

IT 625417-12-1P  
RL: PRP (Properties); SPN (Synthetic preparation); TEM  
(Technical or engineered material use); PREP (Preparation); USES (Uses)  
(polymers for photoresist compns. and patterning process)

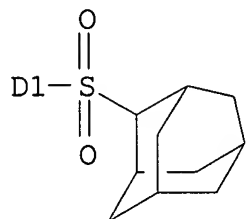
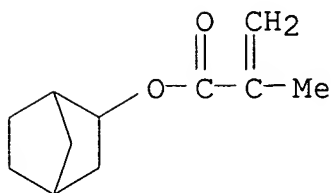
RN 625417-12-1 CAPLUS  
CN 2-Propenoic acid, 2-methyl-,  
2-methyltricyclo[3.3.1.1<sup>3,7</sup>]dec-2-yl ester,  
polymer with 5(or 6)-(tricyclo[3.3.1.1<sup>3,7</sup>]dec-2-ylsulfonyl)bicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate (9CI)  
(CA INDEX  
NAME)

CM 1

CRN 625417-11-0

CMF C21 H30 O4 S

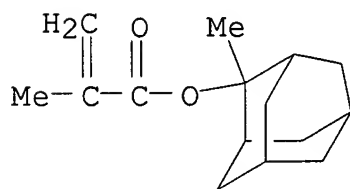
CCI IDS



CM 2

CRN 177080-67-0

CMF C15 H22 O2



L4 ANSWER 8 OF 48 CAPLUS COPYRIGHT 2005 ACS on STN  
 ACCESSION NUMBER: 2004:310383 CAPLUS  
 DOCUMENT NUMBER: 140:347505  
 TITLE: Photo-acid generation type positive-working  
 photoresist composition  
 INVENTOR(S): Sato, Kenichiro  
 PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
 SOURCE: Jpn. Kokai Tokkyo Koho, 79 pp.  
 CODEN: JKXXAF  
 DOCUMENT TYPE: Patent  
 LANGUAGE: Japanese  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

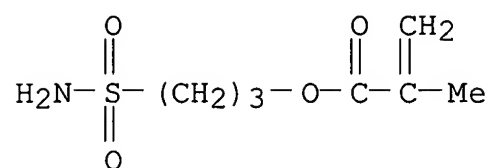
PATENT NO.	KIND	DATE	APPLICATION NO.
JP 2004117883	A2	20040415	JP 2002-281545
20020926			
PRIORITY APPLN. INFO.: 20020926			JP 2002-281545

AB The disclosed photoresist composition contains a photo-acid  
 generating agent  
 and a vinyl polymer comprising first repeating units whose  
 monomer has a  
 specified end group, second repeating units having decomposable  
 group  
 protected by alicyclic structure, and third repeating units  
 having acid  
 having alicyclic alc. moiety. The photoresist composition has  
 good sensitivity  
 towards ArF excimer laser radiation and give fine line patterns  
 without  
 undesirable bridging.

IT **680223-06-7P**  
 RL: SPN (Synthetic preparation); TEM (Technical or engineered  
 material  
 use); PREP (Preparation); USES (Uses)  
 (far UV sensitive photoacid generation type pos. working  
 photoresist  
 containing)

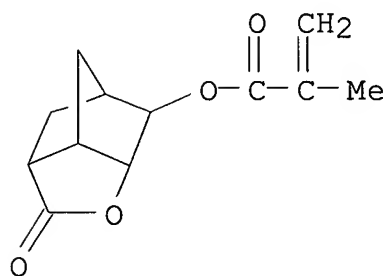
RN 680223-06-7 CAPLUS  
 CN 2-Propenoic acid, 2-methyl-, 3-(aminosulfonyl)propyl ester,  
 polymer with  
 3,5-dihydroxytricyclo[3.3.1.1<sup>3,7</sup>]dec-1-yl 2-methyl-2-propenoate,  
 2-ethyltricyclo[3.3.1.1<sup>3,7</sup>]dec-2-yl 2-methyl-2-propenoate and  
 hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl  
 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CRN 483364-49-4  
CMF C7 H13 N O4 S



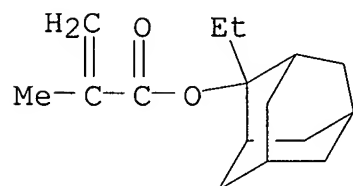
CM 2

CRN 254900-07-7  
CMF C12 H14 O4



CM 3

CRN 209982-56-9  
CMF C16 H24 O2



CM 4

CRN 115522-15-1  
CMF C14 H20 O4

